

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 - 5 (Cancelled).

6. (Currently amended) A method for producing an epitaxial wafer by depositing a film of epitaxial layer through an epitaxial growth over a top surface of a silicon wafer, said method comprising:

a ~~fourth~~ cleaning step for cleaning a top and a back surfaces of a silicon wafer with a SC-1 liquid and a SC-2 liquid;

a ~~fifth~~ hydrophobicating cleaning step, after said ~~fourth~~ cleaning step, for cleaning said back surface of said silicon wafer to be a water repellent surface; and

a ~~sixth~~ hydrophilicating cleaning step for cleaning said top surface of said silicon wafer to be a hydrophilic surface, wherein

after said ~~three~~ cleaning, hydrophobicating cleaning, and hydrophilicating cleaning steps of cleaning having been ~~are~~ finished, a film of epitaxial layer is deposited through an epitaxial growth over said top surface of said silicon wafer, and wherein

said hydrophobicating cleaning and said hydrophilicating cleaning are simultaneously performed.

7 (Cancelled).

8. (Currently amended) A The method for producing an epitaxial wafer in accordance with claim 6, in which a contact angle of said hydrophilic surface is 20° or smaller and a contact angle of said water repellent surface is 30°or greater.

9 (Cancelled).

10. (Currently Amended) A The method for producing an epitaxial wafer in accordance with claim 6, in which said ~~sixth~~ hydrophilicating cleaning step provides a cleaning by a combination of a sponge brush with a purified water.

11 - 12 (Cancelled).

13. (Currently amended) A The method for producing an epitaxial wafer in accordance with claim [[2]] 6, in which said ~~second and said third~~ cleaning steps provide the hydrophobicating cleaning is a cleaning by using at least either one of an HF solution or BHF solution.

14. (Currently amended) A The method for producing an epitaxial wafer in accordance with claim [[3]] 8, in which said ~~second and said third~~ cleaning steps provide the hydrophobicating cleaning is a cleaning by using at least either one of an HF solution or BHF solution.

15. (Currently amended) A The method for producing an epitaxial wafer in accordance with claim [[4]] 10, in which said ~~second and said third hydrophobicating~~ cleaning steps is a provide the cleaning by using at least either one of an HF solution or BHF solution.

16 - 18 (Cancelled).

19. (New) The method for producing an epitaxial wafer in accordance with claim 8, in which said hydrophilicating cleaning provides a cleaning by a combination of a sponge brush with a purified water.

20. (New) The method for producing an epitaxial wafer in accordance with claim 19, in which said hydrophobicating cleaning is a cleaning using an HF solution or BHF solution.